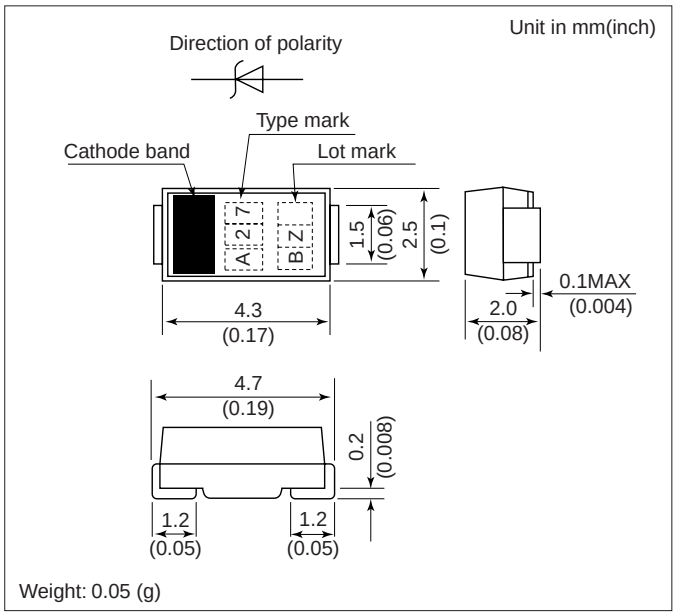
DAM1MA

FEATURES

- High transient reverse power capability suitable for protecting automobile electronic components etc.
- High heat-resistant due to glass passivation.

OUTLINE DRAWING



Weight: 0.05 (g)

ABSOLUTE MAXIMUM RATINGS

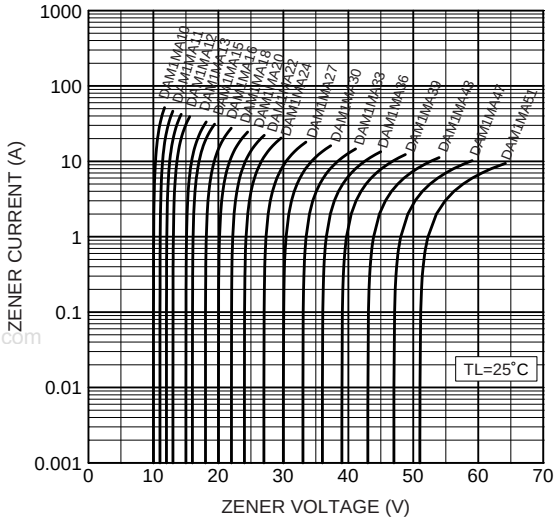
Items	Symbols	Units	Ratings
Non-Repetitive Peak Reverse One-Cycle Dissipation	P_{RSM}	W	600(Rectangular pulse t=0.1ms T_i=25°C start)
Operating Junction Temperature	T_j	°C	-40 ~ +150
Storage Temperature	T_{stg}	°C	-40 ~ +150
DC Reverse Voltage	V_{DC}	V	Refer to characteristics column

CHARACTERISTICS(T_L=25°C)

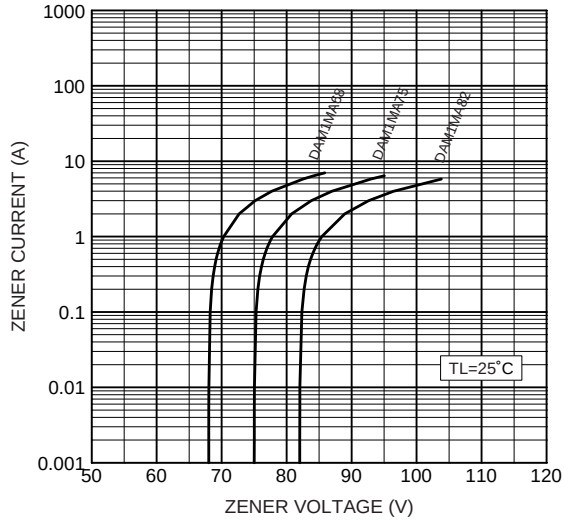
Type	DC Reverse Voltage V_{DC} (V)	Characteristics				Maximum Reverse Current	
		Zener Voltage Vz (V)		Maximum Dynamic Impedance Zz (ohm)	Test Current Iz (mA)	I_{RRM} (μA)	V_R (V)
		Minimum	Maximum				
DAM1MA10	7	9.4	10.6	15	25	10	7
DAM1MA11	8	10.4	11.6	15	25	10	8
DAM1MA12	9	11.4	12.7	15	25	10	9
DAM1MA13	10	12.4	14.1	15	25	10	10
DAM1MA15	11	13.5	15.6	15	25	10	11
DAM1MA16	12	15.3	17.1	15	15	10	12
DAM1MA18	13	16.8	19.1	15	15	10	13
DAM1MA20	14	18.8	21.2	15	15	10	14
DAM1MA22	16	20.8	23.3	15	15	10	16
DAM1MA24	18	22.7	25.6	15	10	10	18
DAM1MA27	20	25.1	28.9	15	10	10	20
DAM1MA30	22	28.0	32.0	15	10	10	22
DAM1MA33	24	31.0	35.0	15	10	10	24
DAM1MA36	26	33.4	38.6	15	10	10	26
DAM1MA39	28	36.1	41.9	30	10	10	28
DAM1MA43	31	39.8	46.2	30	6	10	31
DAM1MA47	34	43.3	50.7	30	6	10	34
DAM1MA51	37	46.9	55.1	30	6	10	37
DAM1MA68	49	61.2	74.8	60	4	5	55
DAM1MA75	54	67.5	82.5	60	4	5	61
DAM1MA82	59	73.8	90.2	60	3	5	66

DAM1MA

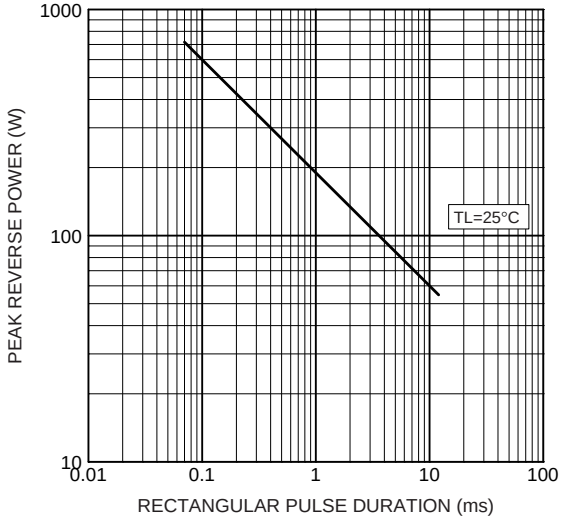
Typical zener characteristics (Vz:10~51V)



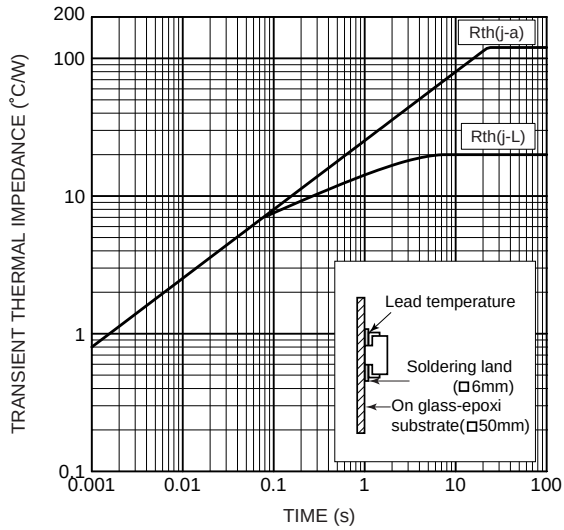
Typical zener characteristics (Vz:68~82V)



Typical reverse power characteristic
(Rectangular pulse non-repetitive)



Transient thermal impedance



HITACHI POWER SEMICONDUCTORS

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